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DATA SHEET

Atomic Layer Deposition (ALD)

Beneq

TFS200

copt-zentrum.de

Universität zu Köln

Technical Data — Atomic Layer Deposition (ALD)

Company	**Beneq**
Model	**TFS200**
Application:	Thin-film deposition, encapsulation
Process type:	Thermal ALD Plasma-Enhanced ALD Face-up and Face-down
Material:	Al_2O_3, TiO_2
Substrat type:	Up to 200 mm wafer Up to 200 x 200 mm² 3D parts
Substrat temperatur range:	25 - 350 °C
Liquid sources:	Up to 4
Gas lines:	Up to 8
Plasma option (PEALD):	Power: 300 W, Type: Capacitively coupled plasma (CCP)
Control system:	PLC control with PC user interface
Integration:	Glove box Load-Lock Cluster

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